Sunghyun Kim

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Research Interest

- · Solar cell and battery simulations from first-principles
- · Carrier lifetime and non-radiative carrier recombination via the Shockley-Read-Hall process
- First-principles calculation and tight-binding modelling of nanostructures and defects in semiconductors
- Material design thorough computational search

Education

- Ph.D. in Physics: KAIST, Republic of Korea, 2016
 (Dissertation: Theoretical study on doping efficiency in silicon nanowires supervised by Prof. K. J. Chang)
- B.S. in Physics: KAIST, Republic of Korea, 2010

Academic Research Experience

- Postdoctoral Research Associate, Department of Materials, Imperial College London, 2017 -Present (PI Prof. Aron Walsh)
- Postdoctoral Research Associate, Department of Physics, KAIST, 2016 2017 (PI Prof. K. J. Chang)
- Undergraduate internship, Department of Physics, University of Cambridge, 2006 (Advised by Dr. Pietro Cicuta)

Technical Skill

- First-principles calculations within the Density Functional Theory (DFT) framework and tight-binding modeling
- Experience in molecular dynamics simulations and finite-difference modeling
- Experience in VASP, QE, Wannier90, LAMMPS, GULP, Phonopy, etc.
- Programing: Python, Julia, C/C++, FORTRAN

Extracurricular Activities

- United Nations peacekeeping mission (UNIFIL)
- Swimming

Publications

- 1. Sunghyun Kim, Samantha N. Hood, and Aron Walsh, Anharmonic Lattice Relaxation during Non-radiative Carrier Capture arXiv:1904.01348.
- 2. Sunghyun Kim, Ji-Sang Park, Samantha N. Hood, and Aron Walsh, Lone-pair effect on carrier capture in Cu₂ZnSnS₄ solar cells J. Mater. Chem. A, 7, 2686 (2019).
- 3. Ji-Sang Park, Sunghyun Kim, Samantha N. Hood, and Aron Walsh, Open-circuit voltage deficit in Cu₂ZnSnS₄ solar cells by interface bandgap narrowing Appl. Phys. Lett. 113, 212103 (2018).
- 4. Ji-Sang Park, Sunghyun Kim, and Aron Walsh, Stability and electronic properties of planar defects in quaternary I₂-II-IV-VI₄ semiconductors J. Appl. Phys. 124 165705 (2018).
- 5. MinJoong Kim, Sunghyun Kim, Dong Hoon Song, Se Kwon Oh, Kee Joo Chang, and Eun Ae Cho, Promotion of electrochemical oxygen evolution reaction by chemical coupling of cobalt to molybdenum carbide Appl. Catal. B 227, 340 (2018).
- 6. Ji-Sang Park, Sunghyun Kim, Zijuan Xie, and Aron Walsh, Point defect engineering in thin-film solar cells, Nat. Rev. Mat. 3, 194 (2018).
- 7. Bartomeu Monserrat, Ji-Sang Park, Sunghyun Kim and Aron Walsh, Role of electron-phonon coupling and thermal expansion on band gaps, carrier mobility, and interfacial offsets in kesterite thin-film solar cells, Appl. Phys. Lett. 112, 193903 (2018).
- 8. Sunghyun Kim, Ji-Sang Park, and Aron Walsh, Identification of Killer Defects in Kesterite Thin-Film Solar Cells, ACS Energy Lett. 3, 496 (2018).
- Ji-Sang Park, Sunghyun Kim, and Aron Walsh, Opposing effects of stacking faults and antisite domain boundaries on the conduction band edge in kesterite quaternary semiconductors Phys. Rev. Mat. 2, 014602 (2018).
- 10. Woo Hyun Han, **Sunghyun Kim**, In-Ho Lee, and K. J. Chang, **Prediction of Green Phosphorus with Tunable Direct Band Gap and High Mobility**, J. Phys. Chem. Lett. 8, 4627(2017).
- 11. **Sunghyun Kim**, Woo Hyun Han, In-Ho Lee, and K. J. Chang, **Boron Triangular Kagome Lattice with Half-Metallic Ferromagnetism**, Scientific Reports 7, 7279 (2017).
- 12. Ha-Jun Sung, Sunghyun Kim, In-Ho Lee, and K. J. Chang, Semimetallic carbon allotrope with topological nodal line in mixed sp³-sp² bonding networks NPG Asia Materials 9, e361 (2017).
- 13. Woo Hyun Han, Young Jun Oh, Duk-Hyun Choe, **Sunghyun Kim**, In-Ho Lee and Kee Joo Chang, **Three-dimensional buckled honeycomb boron lattice with vacancies as an intermediate phase on the transition pathway from \alpha-B to \gamma-B NPG Asia Materials 9, e400 (2017).**
- 14. Elisabeth Pratidhina, Sunghyun Kim, and K. J. Chang, Design of Dipole-Allowed Direct Band Gaps in Ge/Sn Core-Shell Nanowires, J. Phys. Chem. C 120, 28169 (2016).
- 15. In-Ho Lee, Young Jun Oh, Sunghyun Kim, Jooyoung Lee, and K. J. Chang, Ab initio materials design using conformational space annealing and its application to searching for direct band gap silicon crystals, Comp. Phys. Comm. 203, 110 (2016).
- 16. Young Jun Oh, **Sunghyun Kim**, In-Ho Lee, Jooyoung Lee, and K. J. Chang, **Direct band gap carbon superlattices with efficient optical transition**, Phys. Rev. B 93, 085201 (2016).
- 17. Young Jun Oh, In-Ho Lee, **Sunghyun Kim**, Jooyoung Lee, and K. J. Chang, **Dipole-allowed direct band gap silicon superlattices**, Sci. Rep. 8, 18086 (2015).

- 18. In-Ho Lee, Jooyoung Lee, Young Jun Oh, **Sunghyun Kim**, and K. J. Chang, **Computational search for direct band gap silicon crystals**, Phys. Rev. B 90, 115209 (2014).
- 19. Sunghyun Kim, Ji-Sang Park, and K. J. Chang, Finite-size supercell correction scheme for charged defects in one-dimensional systems, Phys. Rev. B 90, 085435 (2014).
- 20. Sunghyun Kim, Ji-Sang Park, K. J. Chang, Stability and Segregation of B and P Dopants in Si/SiO₂ Core-Shell Nanowires, Nano lett. 12, 5068 (2012).